鼎德丰
DING DE FENG

PNP Silicon Transistor

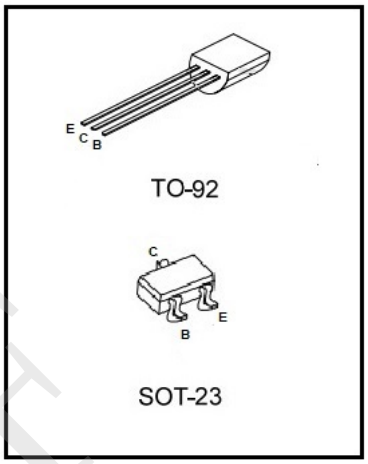
2SA1266

FEATURES

- Low Noise
- Complementary to 2SC3198
- Package:TO-92/SOT-23

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating		Unit
Collector-base voltage	BV_{CBO}	-50		V
Collector-emitter voltage	BV_{CEO}	-50		V
Emitter-base voltage	BV_{EBO}	-5		V
Collector current	I_C	-150		mA
Emitter current	I_E	-150		
Collector Power Dissipation	P_C	SOT-23	0.25	W
		TO-92	0.4	
Junction Temperature	Tj	125		℃
Storage Temperature	Tstg	-55～+125		℃



Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-100μA，I_E=0	-50			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=-1mA，I_B=0	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-100μA，I_C=0	-5			V
collector-base cut-off current	I_{CBO}	V_{CB}=-50V，I_E=0			-0.1	μA
collector-emitter cut-off current	I_{CEO}	V_{CE}=-50V，I_B=0			-0.1	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=-5V，I_C=0			-0.1	μA
DC current gain	H_{FE}	V_{CE}=-6V，I_C=-2mA	70		400	
		V_{CE}=-6，I_C=-150mA	25			
collector-emitter saturation voltage	V_{CESAT}	I_C=-100mA，I_B=-10mA			-0.3	V
Base-Emitter Saturation Voltage	V_{BESAT}	I_C=-100mA，I_B=-10mA			-1.0	
Transition frequency	f_T	V_{CE}=-10V，I_C=-1mA	80			MH_Z
Output Capacitance	C_{OB}	V_{CB}=-10V，I_C=-1mA,f=1MHz			7	pF
Noise Figure	NF	V_{CE}=-6V，I_C=-0.1mA, Rg=10KΩ, f=1KHz			10	dB

Classification of H_{FE}

Rank	2SA1266-O	2SA1266-Y	2SA1266-GR
Range	70-140	120-240	200-400